

BSS63LT1G, NSVBSS63LT1G

High Voltage Transistor

PNP Silicon

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------|-------|------|
| Collector-Emitter Voltage | V_{CEO} | -100 | Vdc |
| Collector-Emitter Voltage $R_{BE} = 10\text{ k}\Omega$ | V_{CER} | -110 | Vdc |
| Collector Current - Continuous | I_C | -100 | mAdc |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|----------------|----------------------------|
| Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 225 1.8 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance Junction-to-Ambient | $R_{\theta JA}$ | 556 | $^\circ\text{C}/\text{W}$ |
| Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 300 2.4 | mW mW/ $^\circ\text{C}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 417 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature | T_J, T_{stg} | -55 to +150 | $^\circ\text{C}$ |

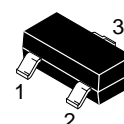
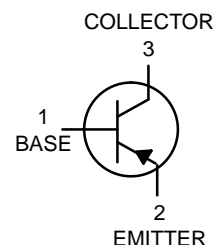
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



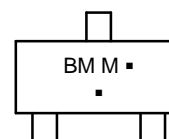
ON Semiconductor®

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SOT-23
CASE 318
STYLE 6

MARKING DIAGRAM



BM = Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|--------------|---------------------|--------------------|
| BSS63LT1G | SOT-23 (Pb-free) | 3000 / Tape & Reel |
| NSVBSS63LT1G | SOT-23 (Pb-free) | 3000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|---|---------------|------|-----|------|-----------------|
| OFF CHARACTERISTICS | | | | | |
| Collector–Emitter Breakdown Voltage ($I_C = -100\ \mu\text{Adc}$) | $V_{(BR)CEO}$ | -100 | - | - | Vdc |
| Collector–Emitter Breakdown Voltage ($I_C = -10\ \mu\text{Adc}$, $I_E = 0$, $R_{BE} = 10\ \text{k}\Omega$) | $V_{(BR)CER}$ | -110 | - | - | Vdc |
| Collector–Base Breakdown Voltage ($I_E = -10\ \mu\text{Adc}$, $I_C = 0$) | $V_{(BR)CBO}$ | -110 | - | - | Vdc |
| Emitter–Base Breakdown Voltage ($I_E = -10\ \mu\text{Adc}$) | $V_{(BR)EBO}$ | -6.0 | - | - | Vdc |
| Collector Cutoff Current ($V_{CB} = -90\ \text{Vdc}$, $I_E = 0$) | I_{CBO} | - | - | -100 | nAdc |
| Collector Cutoff Current ($V_{CE} = -110\ \text{Vdc}$, $R_{BE} = 10\ \text{k}\Omega$) | I_{CER} | - | - | -10 | μAdc |
| Emitter Cutoff Current ($V_{EB} = -6.0\ \text{Vdc}$, $I_C = 0$) | I_{EBO} | - | - | -200 | nAdc |

ON CHARACTERISTICS

| | | | | | |
|---|---------------|----------|--------|--------|------|
| DC Current Gain ($I_C = -10\ \text{mAdc}$, $V_{CE} = -1.0\ \text{Vdc}$) ($I_C = -25\ \text{mAdc}$, $V_{CE} = -1.0\ \text{Vdc}$) | h_{FE} | 30 30 | - - | - - | - |
| Collector–Emitter Saturation Voltage ($I_C = -25\ \text{mAdc}$, $I_B = -2.5\ \text{mAdc}$) | $V_{CE(sat)}$ | - | - | -250 | mVdc |
| Base–Emitter Saturation Voltage ($I_C = -25\ \text{mAdc}$, $I_B = -2.5\ \text{mAdc}$) | $V_{BE(sat)}$ | - | - | -900 | mVdc |

SMALL–SIGNAL CHARACTERISTICS

| | | | | | |
|---|-------|----|----|----|-----|
| Current–Gain–Bandwidth Product ($I_C = -25\ \text{mAdc}$, $V_{CE} = -5.0\ \text{Vdc}$, $f = 20\ \text{MHz}$) | f_T | 50 | 95 | - | MHz |
| Case Capacitance ($I_E = I_C = 0$, $V_{CB} = -10\ \text{Vdc}$, $f = 1.0\ \text{MHz}$) | C_C | - | - | 20 | pF |
| Noise Figure ($I_C = -0.2\ \text{mA}$, $V_{CE} = -5.0\ \text{Vdc}$, $R_g = 2\ \text{k}\Omega$, $f = 1.0\ \text{kHz}$, $BW = 200\ \text{Hz}$) | NF | - | - | 10 | dB |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

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TYPICAL CHARACTERISTICS

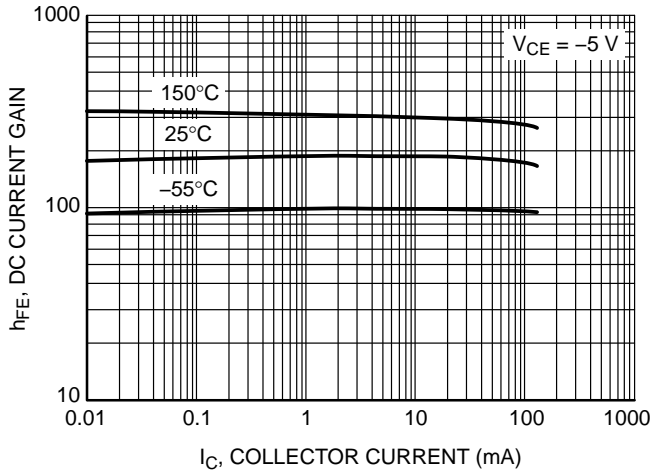


Figure 1. DC Current Gain

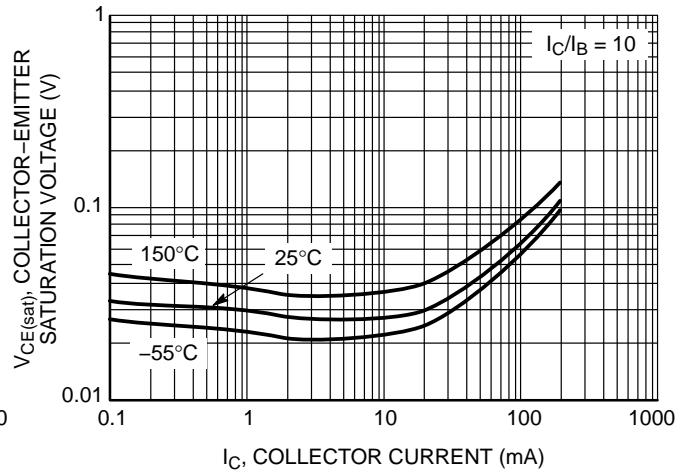


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

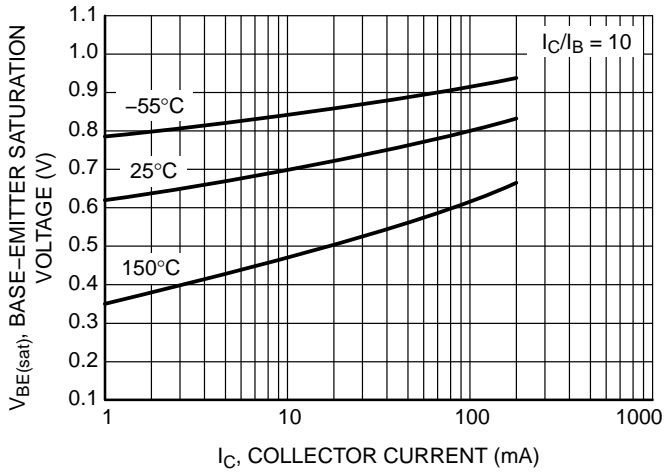


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

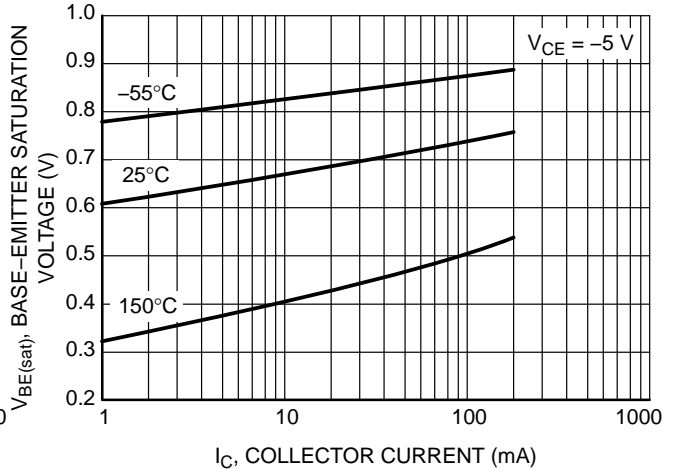


Figure 4. Base-Emitter Voltage vs. Collector Current

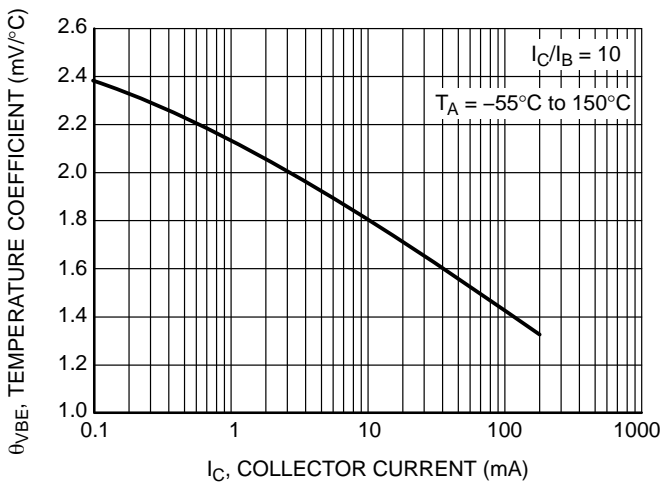


Figure 5. Base-Emitter Temperature Coefficient

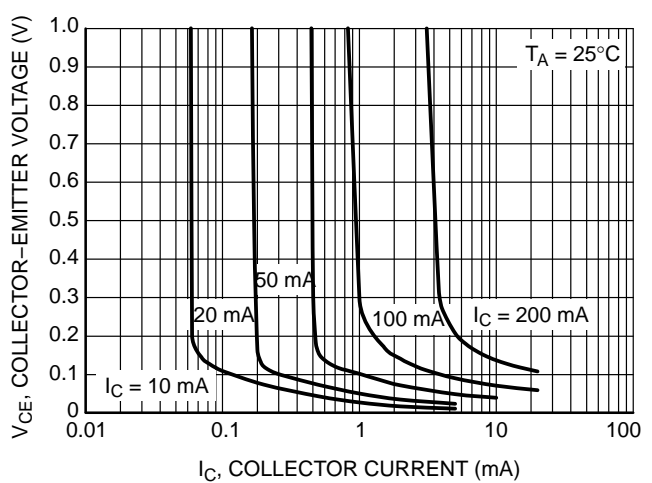


Figure 6. Collector Saturation Region

BSS63LT1G, NSVBSS63LT1G

TYPICAL CHARACTERISTICS

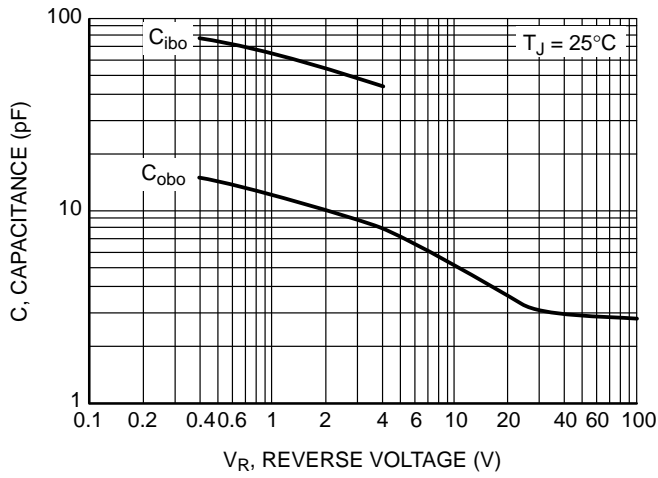


Figure 7. Capacitance

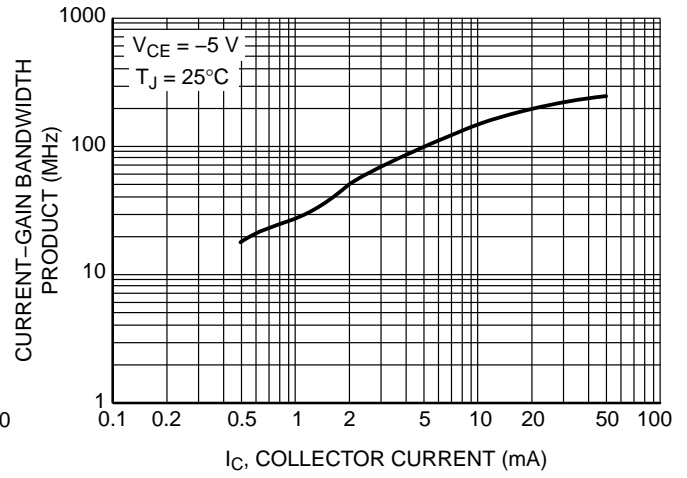


Figure 8. Current-Gain Bandwidth Product

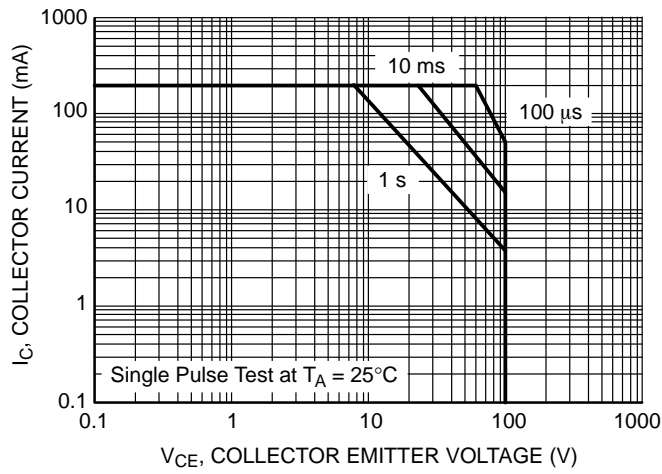
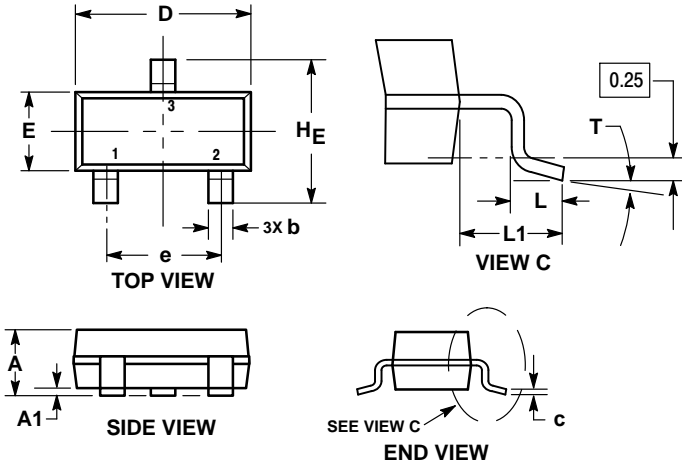


Figure 9. Safe Operating Area

BSS63LT1G, NSVBSS63LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR



NOTES:

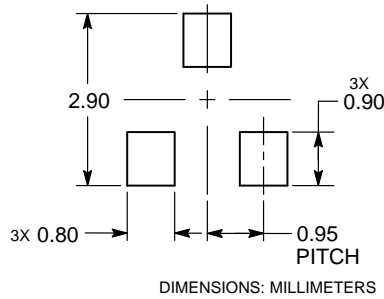
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| c | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| HE | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| T | 0° | — | 10° | 0° | — | 10° |

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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